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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	200MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8306vmacdca

Email: info@E-XFL.COM

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- Programmable highest priority request
- Six groups of interrupts with programmable priority
- External and internal interrupts directed to host processor
- Unique vector number for each interrupt source
- Enhanced secure digital host controller (eSDHC)
 - Compatible with the SD Host Controller Standard Specification Version 2.0 with test event register support
 - Compatible with the MMC System Specification Version 4.2
 - Compatible with the SD Memory Card Specification Version 2.0 and supports the high capacity SD memory card
 - Compatible with the SD Input/Output (SDIO) Card Specification, Version 2.0
 - Designed to work with SD Memory, miniSD Memory, SDIO, miniSDIO, SD Combo, MMC, MMC*plus*, and RS-MMC cards
 - Card bus clock frequency up to 33.33 MHz.
 - Supports 1-/4-bit SD and SDIO modes, 1-/4-bit modes
 - Up to 133 Mbps data transfer for SD/SDIO/MMC cards using 4 parallel data lines
 - Supports block sizes of 1 ~ 4096 bytes
- Universal serial bus (USB) dual-role controller
 - Designed to comply with Universal Serial Bus Revision 2.0 Specification
 - Supports operation as a stand-alone USB host controller
 - Supports operation as a stand-alone USB device
 - Supports high-speed (480-Mbps), full-speed (12-Mbps), and low-speed (1.5-Mbps) operations. Low speed is only supported in host mode.
- FlexCAN module
 - Full implementation of the CAN protocol specification version 2.0B
 - Up to 64 flexible message buffers of zero to eight bytes data length
 - Powerful Rx FIFO ID filtering, capable of matching incoming IDs
 - Selectable backwards compatibility with previous FlexCAN module version
 - Programmable loop-back mode supporting self-test operation
 - Global network time, synchronized by a specific message
 - Independent of the transmission medium (an external transceiver is required)
 - Short latency time due to an arbitration scheme for high-priority messages
- Dual I²C interfaces
 - Two-wire interface
 - Multiple-master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
 - I²C1 can be used as the boot sequencer



Power Characteristics



Figure 3. MPC8306 Power-Up Sequencing Example

3 Power Characteristics

The typical power dissipation for this family of MPC8306 devices is shown in the following table.

Core Frequency (MHz)	QUICC Engine Frequency (MHz)	CSB Frequency (MHz)	Typical	Maximum	Unit	Note
133	133	133	0.272	0.618	W	1, 2, 3
200	233	133	0.291	0.631	W	1, 2, 3
266	233	133	0.451	0.925	W	1, 2, 3
333	233	133	0.471	0.950	W	1, 2, 3

 Table 5. MPC8306 Power Dissipation

Notes:

1. The values do not include I/O supply power (OV_{DD} and GV_{DD}), but it does include V_{DD} and AV_{DD} power. For I/O power values, see Table 6.

 Typical power is based on a nominal voltage of V_{DD} = 1.0 V, ambient temperature, and the core running a Dhrystone benchmark application. The measurements were taken on the evaluation board using WC process silicon.

3. Maximum power is based on a voltage of V_{DD} = 1.05 V, WC process, a junction T_J = 105°C, and a smoke test code.



RESET Initialization

4.2 AC Electrical Characteristics

The primary clock source for the MPC8306 is SYS_CLK_IN. The following table provides the clock input (SYS_CLK_IN) AC timing specifications for the MPC8306. These specifications are also applicable for QE_CLK_IN.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Note
SYS_CLK_IN frequency	f _{SYS_CLK_IN}	24	_	66.67	MHz	1
SYS_CLK_IN cycle time	t _{SYS_CLK_IN}	15	—	41.6	ns	_
SYS_CLK_IN rise and fall time	t _{KH} , t _{KL}	1.1	_	2.8	ns	2
SYS_CLK_IN duty cycle	t _{КНК} /tsys_clk_ IN	40	—	60	%	3
SYS_CLK_IN jitter	_	_	_	±150	ps	4, 5

Table 8	B. SYS_	CLK	IN AC	Timing	Specifications
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Notes:

- 1. **Caution:** The system, core and QUICC Engine block must not exceed their respective maximum or minimum operating frequencies.
- 2. Rise and fall times for SYS_CLK_IN are measured at 0.33 and 2.97 V.
- 3. Timing is guaranteed by design and characterization.
- 4. This represents the total input jitter—short term and long term—and is guaranteed by design.
- 5. The SYS_CLK_IN driver's closed loop jitter bandwidth should be < 500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYS_CLK_IN drivers with the specified jitter.
- 6. Spread spectrum is allowed up to 1% down-spread @ 33kHz (max rate).

5 **RESET** Initialization

This section describes the AC electrical specifications for the reset initialization timing requirements of the MPC8306. The following table provides the reset initialization AC timing specifications for the reset component(s).

Parameter/Condition	Min	Max	Unit	Note
Required assertion time of HRESET to activate reset flow	32		t _{SYS_CLK_IN}	1
Required assertion time of PORESET with stable clock applied to SYS_CLK_IN	32		t _{SYS_CLK_IN}	1
HRESET assertion (output)	512	_	t _{SYS_CLK_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:3]) with respect to negation of PORESET	4	_	t _{SYS_CLK_IN}	1, 2
Input hold time for POR config signals with respect to negation of HRESET	0	_	ns	1, 2

Table 9. RESET Initialization Timing Specifications

Notes:

1. t_{SYS_CLK_IN} is the clock period of the input clock applied to SYS_CLK_IN. For more details, see the *MPC8306 PowerQUICC II Pro Integrated Communications Processor Family Reference Manual.*

2. POR configuration signals consist of CFG_RESET_SOURCE[0:3].



Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Мах	Unit	Note
Output high current (V _{OUT} = 1.35 V)	I _{OH}	-13.4	_	mA	_
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	_	mA	

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. MVREF is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MVREF may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREF. This rail should track variations in the DC level of MVREF.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

The following table provides the DDR2 capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.100 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = GV_{DD} ÷ 2,

V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR2 SDRAM interface.

6.2.1 DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM ($GV_{DD}(typ) = 1.8 V$).

Table 14. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
AC input low voltage	V _{IL}	—	MVREF – 0.25	V	—
AC input high voltage	V _{IH}	MVREF + 0.25	_	V	—

The following table provides the input AC timing specifications for the DDR2 SDRAM interface.

Table 15. DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol	Min	Мах	Unit	Note
Controller skew for MDQS—MDQ/MDM	t _{CISKEW}			ps	1, 2



Table 15. DDR2 SDRAM Input AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8V \pm 100mV.

Parameter	Symbol	Min	Мах	Unit	Note
266 MHz		-750	750		

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.

 The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: t_{DISKEW} = ±(T/4 – abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.

The following figure shows the input timing diagram for the DDR controller.



Figure 4. DDR Input Timing Diagram

6.2.2 DDR2 SDRAM Output AC Timing Specifications

The following table provides the output AC timing specifications for the DDR2 SDRAM interfaces.

Table 16. DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8V \pm 100mV.

Parameter	Symbol ¹	Min	Max	Unit	Note
MCK cycle time, (MCK/MCK crossing)	t _{MCK}	5.988	8	ns	2
ADDR/CMD output setup with respect to MCK	t _{DDKHAS}			ns	3
266 MHz		2.5	—		
ADDR/CMD output hold with respect to MCK	t _{DDKHAX}			ns	3
266 MHz		2.5	—		
MCS output setup with respect to MCK	t _{DDKHCS}			ns	3
266 MHz		2.5	—		

The following figure provides the AC test load for the local bus.



The following figures show the local bus signals. These figures has been given indicate timing parameters only and do not reflect actual functional operation of interface.





Local Bus







The following figure shows the RMII transmit AC timing diagram.



Figure 15. RMII Transmit AC Timing Diagram

8.2.2.2 RMII Receive AC Timing Specifications

The following table provides the RMII receive AC timing specifications.

Table 23. RMII Receive AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3 V ± 300mV.

Parameter/Condition	Symbol ¹	Min	Typical	Мах	Unit
REF_CLK clock period	t _{RMX}	_	20	—	ns
REF_CLK duty cycle	t _{RMXH} /t _{RMX}	35	_	65	%
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	t _{RMRDVKH}	4.0	_	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	t _{RMRDXKH}	2.0	_	—	ns
REF_CLK clock rise V _{IL} (min) to V _{IH} (max)	t _{RMXR}	1.0	_	4.0	ns
REF_CLK clock fall time $V_{IH}(max)$ to $V_{IL}(min)$	t _{RMXF}	1.0		4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of t_{(first three letters of functional block)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{RMRDVKH} symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, t_{RMRDXKL} symbolizes RMII receive timing (RMR) with respect to the tinvalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).



HDLC

9.2 TDM/SI AC Timing Specifications

The following table provides the TDM/SI input and output AC timing specifications.

Table 29. TDM/SI AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
TDM/SI outputs—External clock delay	t _{SEKHOV}	2	14	ns
TDM/SI outputs—External clock High Impedance	t _{SEKHOX}	2	10	ns
TDM/SI inputs—External clock input setup time	t _{SEIVKH}	5	—	ns
TDM/SI inputs—External clock input hold time	t _{SEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of QE_CLK_IN to the 50% level of the signal. Timings are measured at the pin.

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{SEKHOX} symbolizes the TDM/SI outputs external timing (SE) for the time t_{TDM/SI} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
</sub></sub>

The following figure provides the AC test load for the TDM/SI.



Figure 20. TDM/SI AC Test Load

The following figure represents the AC timing from Table 29. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.



Figure 21. TDM/SI AC Timing (External Clock) Diagram

10 HDLC

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), of the MPC8306.



10.1 HDLC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306 HDLC protocol.

Table 30. HDLC D	OC Electrical	Characteristics
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Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -2.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.5	V
Input high voltage	V _{IH}	—	2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0 \ V \leq \ V_{IN} \leq OV_{DD}$	_	±5	μA

10.2 HDLC AC Timing Specifications

The following table provides the input and output AC timing specifications for HDLC protocol.

Table 31. HDLC AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock delay	t _{HIKHOV}	0	9	ns
Outputs—External clock delay	t _{HEKHOV}	1	12	ns
Outputs—Internal clock high impedance	t _{HIKHOX}	0	5.5	ns
Outputs—External clock high impedance	t _{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t _{HIIVKH}	9	_	ns
Inputs—External clock input setup time	t _{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t _{HIIXKH}	0	—	ns
Inputs—External clock input hold time	t _{HEIXKH}	1	_	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of QE_CLK_IN to the 50% level of the signal. Timings are measured at the pin.

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
</sub>

The following figure provides the AC test load.



Figure 22. AC Test Load



is the active edge.

Figure 23 and Figure 24 represent the AC timing from Table 31. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge

The following figure shows the timing with external clock.



Figure 23. AC Timing (External Clock) Diagram

The following figure shows the timing with internal clock.



Figure 24. AC Timing (Internal Clock) Diagram







JTAG

The following figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.



The following figure shows the SPI timing in master mode (internal clock).



Figure 35. SPI AC Timing in Master Mode (Internal Clock) Diagram

20 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1[™] (JTAG) interface of the MPC8306.

20.1 JTAG DC Electrical Characteristics

The following table provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8306.

Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -6.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 6.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V

Table 50. JTAG Interface DC Electrical Characteristics



Package and Pin Listings

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MA[8]	T1	0	GV _{DD}	
MEMC_MA[9]	P4	0	GV _{DD}	
MEMC_MA[10]	L4	0	GV _{DD}	_
MEMC_MA[11]	T2	0	GV _{DD}	
MEMC_MA[12]	U1	0	GV _{DD}	_
MEMC_MA[13]	U2	0	GV _{DD}	
MEMC_MWE_B	K1	0	GV _{DD}	
MEMC_MRAS_B	K2	0	GV _{DD}	_
MEMC_MCAS_B	J1	0	GV _{DD}	_
MEMC_MCS_B[0]	J4	0	GV _{DD}	_
MEMC_MCS_B[1]	H1	0	GV _{DD}	_
MEMC_MCKE[0]	U4	0	GV _{DD}	
MEMC_MCK[0]	V1	0	GV _{DD}	_
MEMC_MCK_B[0]	W1	0	GV _{DD}	_
MEMC_MODT[0]	H2	0	GV _{DD}	
MEMC_MODT[1]	H4	0	GV _{DD}	_
MEMC_MVREF	L8		GV _{DD}	_
Loc	al Bus Controller Interfac	e		<u> </u>
LAD[0]	B7	IO	OV _{DD}	—
LAD[1]	D9	IO	OV _{DD}	_
LAD[2]	A6	IO	OV _{DD}	_
LAD[3]	B8	IO	OV _{DD}	_
LAD[4]	A7	IO	OV _{DD}	_
LAD[5]	A8	IO	OV _{DD}	_
LAD[6]	A9	IO	OV _{DD}	_
LAD[7]	D10	IO	OV _{DD}	_
LAD[8]	B10	IO	OV _{DD}	_
LAD[9]	A10	IO	OV _{DD}	_
LAD[10]	B11	IO	OV _{DD}	_
LAD[11]	D12	IO	OV _{DD}	
LAD[12]	D11	IO	OV _{DD}	_
LAD[13]	A11	IO	OV _{DD}	_
LAD[14]	A12	IO	OV _{DD}	—
LAD[15]	B13	IO	OV _{DD}	—
LA[16]	A13	IO	OV _{DD}	—

Table 52. MPC8306 Pinout Listing (continued)



Package and Pin Listings

Signal	Package Pin Number	Pin Type	Power Supply	Notes
V _{DD}	H8,H9,H10,H11,H12,H1 3,H14,H15,H16,J8,J16,K 8,K16,M8,N16,P8,P16,R 8,R16,T8,T9,T10,T11,T1 2,T13,T14,T15,T16	_	_	_
VSS	A1,B4,B6,B9,B12,B15,B 18,B21,C22,D2,D5,D18, D20,F2,F22,J2,J9,J10,J 11,J12,J13,J14,J15,J22, K4,K9,K10,K11,K12,K13 ,K14,K15,L9,L10,L11,L1 2,L13,L14,L15,M2,M9,M 10,M11,M12,M13,M14,M 15,M22,N9,N10,N11,N1 2,N13,N14,N15,P9,P10, P11,P12,P13,P14,P15,R 2,R9,R10,R11,R12,R13, R14,R15,R22,T4,V2,V19 ,V22,W4,Y19,AA2,AA22, AB4,AB6,AB9,AB12,AB1 5,AB18,AB21,AC1,AC23	_	_	_
NC	A23	_	_	_
Notes 1. This pin is an open drain signal. A weak pull-u 2. This pin is an open drain signal. A weak pull-u	p resistor (1 kΩ) should be p p resistor (2-10 kΩ) should b	laced on this pir e placed on this	n to OV _{DD} pin to OV _{DD}	1

Table 52. MPC8306 Pinout Listing (continued)

3. This pin has weak pull-up that is always enabled.



In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. These units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset.

The following table specifies which units have a configurable clock frequency. For detailed description, refer to the "System Clock Control Register (SCCR)" section in the *MPC8306 PowerQUICC II Pro Integrated Communications Processor Family Reference Manual.*

Table 53. Configurable Clock Units

Unit	Default Frequency	Options
I2C,SDHC, USB, DMA Complex	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3

NOTE

Setting the clock ratio of these units must be performed prior to any access to them.

The following table provides the maximum operating frequencies for the MPC8306 MAPBGA under recommended operating conditions (see Table 2).

Table 54. Operating Frequencies for MAPBGA

Characteristic ¹	Max Operating Frequency	Unit
e300 core frequency (<i>core_clk</i>)	266	MHz
Coherent system bus frequency (<i>csb_clk</i>)	133	MHz
QUICC Engine frequency (<i>qe_clk</i>)	233	MHz
DDR2 memory bus frequency (MCLK) ²	167	MHz
Local bus frequency (LCLK <i>n</i>) ³	66	MHz

Notes:

1. The SYS_CLK_IN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting csb_clk, MCLK, LCLK, and core_clk frequencies do not exceed their respective maximum or minimum operating frequencies.

2. The DDR2 data rate is 2× the DDR2 memory bus frequency.

3. The local bus frequency is 1/2, 1/4, or 1/8 of the lb_clk frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the csb_clk frequency (depending on RCWL[LBCM]).

22.2 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 55 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = $2 \times (CSB \text{ frequency}) \times (System PLL VCO divider)$. The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz.

As described in Section 22, "Clocking," the LBCM, DDRCM, and SPMF parameters in the reset configuration word low select the ratio between the primary clock input (*SYS_CLK_IN*) and the internal



RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

Table 55. System PLL Multiplication Factors

coherent system bus clock (*csb_clk*). The following table shows the expected frequency values for the CSB frequency for selected *csb_clk* to *SYS_CLK_IN* ratios.

			SYS_CLK_IN(MHz)	
SPMF	csb_clk : sys_clk_in Ratio	25	33.33	66.67
		cst	_clk Frequency (M	Hz)
0010	2:1			133
0011	3:1			
0100	4:1		133	
0101	5:1	125	167	
0110	6:1			

Table 56. CSB Frequency Options

22.3 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). The following table shows the encodings for RCWL[COREPLL]. COREPLL values not listed, and should be considered reserved.

Table 57. e300 Core PLL Configuration

RCWL[COREPLL]			core clk: csh clk Patio	
0-1	2-5	6		VCO Dividei
nn	0000	n	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)
00	0001	0	1:1	÷2
01	0001	0	1:1	÷4
10	0001	0	1:1	÷8
11	0001	0	1:1	÷8



Clocking

RCWL[COREPLL]			coro alk: ash alk Patio			
0-1	2-5	6				
00	0001	1	1.5:1	÷2		
01	0001	1	1.5:1	÷ 4		
10	0001	1	1.5:1	÷8		
11	0001	1	1.5:1	÷ 8		
00	0010	0	2:1	÷ 2		
01	0010	0	2:1	÷ 4		
10	0010	0	2:1	÷8		
11	0010	0	2:1	÷ 8		
00	0010	1	2.5:1	÷ 2		
01	0010	1	2.5:1	÷ 4		
10	0010	1	2.5:1	÷8		
11	0010	1	2.5:1	÷8		
00	0011	0	3:1	÷2		
01	0011	0	3:1	÷ 4		
10	0011	0	3:1	÷8		
11	0011	0	3:1	÷8		

Table 57. e300 Core PLL Configuration (continued)

NOTE

Core VCO frequency = core frequency \times VCO divider. The VCO divider (RCWL[COREPLL[0:1]]), must be set properly so that the core VCO frequency is in the range of 400–800 MHz.

22.4 QUICC Engine PLL Configuration

The QUICC Engine PLL is controlled by the RCWL[CEPMF] and RCWL[CEPDF] parameters. The following table shows the multiplication factor encodings for the QUICC Engine PLL.

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF)	
00000–00001	0	Reserved	
00010	0	× 2	
00011	0	× 3	
00100	0	× 4	
00101	0	× 5	
00110	0	× 6	

Table 58. QUICC Engine PLL Multiplication Factors



23 Thermal

This section describes the thermal specifications of the MPC8306.

23.1 Thermal Characteristics

The following table provides the package thermal characteristics for the 369, 19×19 mm MAPBGA of the MPC8306.

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{ ext{ heta}JA}$	39	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{ ext{ heta}JA}$	24	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	R_{\thetaJMA}	32	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	R _{0JMA}	21	°C/W	1, 3
Junction-to-board	—	$R_{ heta JB}$	14	°C/W	4
Junction-to-case	_	$R_{ ext{ heta}JC}$	9	°C/W	5
Junction-to-package top	Natural convection	Ψ_{JT}	2	°C/W	6

Table 61. Package Thermal Characteristics for MAPBGA

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.

3. Per JEDEC JESD51-6 with the board horizontal.

- 4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

23.1.1 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

23.1.2 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta} J_A \times P_D)$$
 Eqn. 1

where:

```
T_J = junction temperature (°C)
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lifetime of the package. Recommended maximum force on the top of the package is 10 lb (4.5 kg) force. If an adhesive attachment is planned, the adhesive should be intended for attachment to painted or plastic surfaces and its performance verified under the application requirements.

23.2.1 Experimental Determination of the Junction Temperature with a Heat Sink

When heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimizing the size of the clearance is important to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface.

From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance using the following equation:

$$T_J = T_C + (R_{\theta JC} \times P_D)$$
 Eqn. 5

where:

 T_C = case temperature of the package (°C) $R_{\theta IC}$ = junction-to-case thermal resistance (°C/W)

 P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8306.

24.1 System Clocking

The MPC8306 includes three PLLs.

- The system PLL (AV_{DD2}) generates the system clock from the externally supplied SYS_CLK_IN input. The frequency ratio between the system and SYS_CLK_IN is selected using the system PLL ratio configuration bits as described in Section 22.2, "System PLL Configuration."
- The e300 core PLL (AV_{DD3}) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in Section 22.3, "Core PLL Configuration."
- The QUICC Engine PLL (AV_{DD1}) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.